



NEIFELD IP DOCKET NO: OSEM-DB3

IN RE APPLICATION OF: Braddock      CONF. NUMBER: 6691

Examiner: KANG

SERIAL NO: 09/636,484

GROUP ART UNIT: 2811

FILED: 08/10/00

TITLE: INTEGRATED TRANSISTOR DEVICES

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

ASSISTANT COMMISSIONER FOR PATENTS  
WASHINGTON, D.C. 20231

Listing of Pending Claims, Specifications, and Figures in Related Applications

CSF-1

US Serial Number: 10/163,506  
Filing Date: 6/6/2002  
Inventor: Braddock  
Neifeld Docket No: OSEM-DB12

CSF - 2

US Serial Number: 10/198,705  
Filing Date: 7/16/2002  
Inventor: Braddock  
Neifeld Docket No: OSEM-DB13

Printed: February 26, 2004 (10:36am)  
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Docket No. OSEM-DB12

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: BRADDOCK

INT APP. NO: 10/163,506

GAU: 2813

FILED: 6/6/2002

EXAMINER: Smoot

FOR: Metal Oxide Compound Semiconductor Integrated Transistor Devices



INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

ASSISTANT COMMISSIONER FOR PATENTS  
ALEXANDRIA, VA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- ☒ The applicant(s) wish to make of record the references listed on the attached PTO-1449. Copies of the listed references are being submitted herewith or, were submitted in the parent or grandparent application, where required, as were either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references, or cited by the examiner.
- ☒ A check is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- ☒ Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), including its specification and claims is attached along with PTO 1449.
- ☐ A check is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

- ☐ Each item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- ☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

PETITION

- ☐ Applicant(s) hereby request consideration of the attached information. A check is attached in the amount of the Petition fee required under 37 CFR §1.17(i)(1).

DEPOSIT ACCOUNT

- ☒ Please charge any additional fees for the papers being filed herewith and for which no check is enclosed herewith, or credit any overpayment to deposit account number 50-2106. A duplicate copy of this sheet is enclosed.

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PATENT TRADEMARK OFFICE

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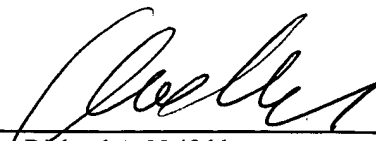
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Respectfully submitted,

  
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BTM

Printed: February 26, 2004 (10:22am)

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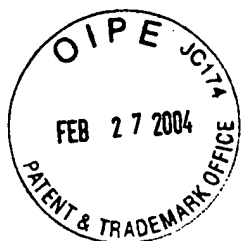
NEIFELD IP LAW REFERENCE FORM LIST OF REFERENCES CITED BY THE APPLICANT (Rev: 5/14/2003)	NEIFELD REF: OSEM-DB3	APPLICATION NO: 09/636,484
	FIRST NAMED INVENTOR: Walter David BRADDOCK	
	FILING DATE: 8/10/2000	GROUP ART UNIT: 2811

### LISTING OF UNITED STATES PATENTS

EXAMINER INITIALS	REFERENCE NUMBER (U SERIES)	PATENT NUMBER	ISSUE DATE	NAME OF PATENTEE OR APPLICANT	PAGE/LINE AND FIGURE/ELEMENT OF RELEVANT MATERIAL AND/OR IDENTIFICATION OF PRIORITY APPLICATION IN WHICH REFERENCE IS CITED
	<del>U-25</del>	5,597,768	<del>1-1997</del>	Passlack et al.	Of Record
	U-26	5,640,751	6-1997	Faria	
	<del>U-27</del>	5,665,658	<del>9-1997</del>	Passlack	Of Record
	<del>U-28</del>	5,693,565	<del>12-1997</del>	Camilletti et al.	Of Record
	U-29	5,729,563	3-1998	Wang et al.	
	<del>U-30</del>	5,767,388	<del>6-1998</del>	Fletcher et al.	Of Record
	U-31	5,805,624	9-1998	Yang et al.	
	<del>U-32</del>	5,821,171	<del>10-1998</del>	Hong et al.	Of Record
	U-33	5,838,708	11-1998	Lin et al.	
	U-34	5,896,408	4-1999	Corzine et al.	
	<del>U-35</del>	5,930,611	<del>7-1999</del>	Okamoto	Of Record
	<del>U-36</del>	5,945,718	<del>8-1999</del>	Passlack et al.	Of Record
	U-37	5,953,362	9-1999	Pamulapati et al.	
	<del>U-38</del>	6,006,582	<del>12-1999</del>	Bhandari et al.	Of Record
	U-39	6,028,693	2-2000	Fork et al.	
	<del>U-40</del>	6,030,453	<del>2-2000</del>	Passlack et al.	Of Record
	U-41	6,045,611	4-2000	Ishii et al.	
	U-42	6,069,908	5-2000	Yuen et al.	
	<del>U-43</del>	6,071,780	<del>6-2000</del>	Okamoto et al.	Of Record
	<del>U-44</del>	6,094,295	<del>7-2000</del>	Passlack et al.	Of Record
	U-45	6,114,079	9-2000	Christian et al.	
	<del>U-46</del>	6,150,677	<del>11-2000</del>	Tanaka et al.	Of Record
	<del>U-47</del>	6,207,976	<del>3-2001</del>	Takahashi et al.	Of Record
	U-48	6,252,896	6-2001	Tan et al.	

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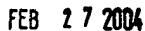
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NEIFELD IP LAW REFERENCE FORM LIST OF REFERENCES CITED BY THE APPLICANT (Rev: 5/14/2003)	NEIFELD REF: OSEM-DB3	APPLICATION NO: 09/636,484
	FIRST NAMED INVENTOR: Walter David BRADDOCK	
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	U-1	3,950,273	4-1976	Jones	
	U-2	4,404,265	9-1983	Manasevit	
	U-3	4,410,902	10-1983	Malik	
	<del>U-4</del>	<del>4,416,952</del>	<del>11-1983</del>	<del>Nishizawa et al.</del>	Of Record
	<del>U-5</del>	<del>4,561,915</del>	<del>12-1985</del>	<del>Mito</del>	Of Record
	U-6	4,624,901	11-1986	Glass	
	U-7	4,671,777	6-1987	van Esdonk et al.	
	U-8	4,685,193	8-1987	Faria et al.	
	<del>U-9</del>	<del>4,745,082</del>	<del>5-1988</del>	<del>Kwok</del>	Of Record
	<del>U-10</del>	<del>4,802,180</del>	<del>1-1989</del>	<del>Brandie, Jr. et al.</del>	Of Record
	<del>U-11</del>	<del>4,843,450</del>	<del>6-1989</del>	<del>Kirchner et al.</del>	Of Record
	<del>U-12</del>	<del>4,859,253</del>	<del>8-1989</del>	<del>Duchanan et al.</del>	Of Record
	<del>U-13</del>	<del>4,935,789</del>	<del>6-1990</del>	<del>Calviello</del>	Of Record
	U-14	4,970,060	11-1990	Belt et al.	
	U-15	5,055,445	10-1991	Belt et al.	
	<del>U-16</del>	<del>5,124,762</del>	<del>6-1992</del>	<del>Childs et al.</del>	Of Record
	U-17	5,170,407	12-1992	Schubert et al.	
	U-18	5,270,798	12-1993	Pao et al.	
	U-19	5,323,053	6-1994	Luryi et al.	
	U-20	5,386,137	1-1995	Dell et al.	
	U-21	5,425,043	6-1995	Holonyak et al.	
	<del>U-22</del>	<del>5,451,548</del>	<del>9-1995</del>	<del>Hunt et al.</del>	Of Record
	U-23	5,491,712	2-1996	Lin et al.	
	<del>U-24</del>	<del>5,550,089</del>	<del>8-1996</del>	<del>Dutta et al.</del>	Of Record
Date:			Examiner's Signature:		



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LIST OF REFERENCES CITED BY THE  
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(Rev: 5/14/2003)

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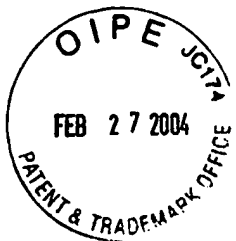
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	FIRST NAMED INVENTOR: Walter David BRADDOCK	
	FILING DATE: 8/10/2000	GROUP ART UNIT: 2811

# LISTING OF NON PATENT LITERATURE

EXAMINER INITIALS	REFERENCE NUMBER (L Series)	PUBLICATION DATE	INCLUDE IN SEQUENCE: Name of first author (in CAPITAL LETTERS), Title in quotation marks, name of publication, date or publication, page numbers, publisher, city of publication, and country of publication	ENGLISH LANGUAGE TRANSLATION ATTACHED? (YES OR NO) AND/OR OR IDENTIFICATION OF PRIORITY APPLICATION IN WHICH REFERENCE IS CITED
	L-1	1994	"1995-1996 Alfa AESAR Catalog," 1994, page 1244, Johnson Matthey Catalog Company, Inc., Ward Hill, MA, US.	
	L-2	6-2001	VURGATMAN et al., "Band Parameters for III-V Semiconductors and Their Alloys," J. Appl. Phys. PP 5816-5875 (June 1, 2001).	Of Record
	L-3	2003	"Gallium Oxide on Gallium Arsenide: Atomic Structure, Materials, and Devices," Chapter 12, either published or scheduled for publication in "Gallium Oxide on Gallium Arsenide: Atomic Structure, Materials, and Devices," in III-IV Semiconductor Heterostructures: Physics and Devices, edited by W.Z. Cai, Transworld Research Publisher, Kerala, India (2003).	Of Record
	L-4	7-1996	PASSLACK et al., "Thermodynamic and photochemical stability of low interface state density Ga <sub>2</sub> O <sub>3</sub> -GaAs structures fabricated by in-situ molecular beam epitaxy", Applied Physics Letters, Vol 69, No 3, pps 302-304, 15 July 1996.	Of Record
	L-5	6-1997	PASSLACK et al., "Recombination velocity at oxide-GaAs interfaces fabricated by in-situ molecular beam epitaxy", Applied Physics Letters, Volume 68, Number 25, pages 3605-3607, 17 June 1997.	Of Record
	L-6	2-1996	PASSLACK et al., "Quasistatic and high frequency capacitance-voltage characterization of Ga <sub>2</sub> O <sub>3</sub> -GaAs structures fabricated by in-situ molecular beam epitaxy", Applied Physics Letters, Volume 68, Number 8, pages 1099-1101, 19 February 1996.	Of Record
	L-7	8-1997	UEDA et al., "Anisotropy of electrical and optical properties in B-Ga <sub>2</sub> O <sub>3</sub> single crystals", Applied Physics Letters, Volume 71, Number 7, Pages 933-935, 18 August 1997.	Of Record
	L-8	6-1997	UEDA et al., "Synthesis and control of conductivity of ultraviolet transmitting B-Ga <sub>2</sub> O <sub>3</sub> single crystals", Applied Physics Letters, Volume 70, Number 26, pages 3561-3563, 30 June 1997.	Of Record
	L-9	2-2000	KHAN et al., "AlGaIn/GaN Metal Oxide Semiconductor Heterostructure Field Effect Transistor", IEEE Electron Device Letters, Volume 21, Number 2, pages 63-65, Feb. 2000.	

Date:	Examiner's Signature:
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